

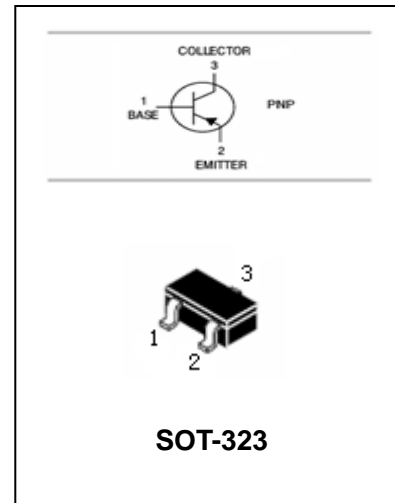
PNP General Purpose Transistor

MMST5401

FEATURES

- Epitaxial planar die construction
- Complementary NPN type available (MMST5551)
- Also available in lead free version

HF



APPLICATIONS

- Ideal for medium power amplification and switching

ORDERING INFORMATION

Type No.	Marking	Package Code
MMST5401	K4M	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	UNIT
V _{CB0}	collector-base voltage	-160	V
V _{CEO}	collector-emitter voltage	-150	V
V _{EB0}	emitter-base voltage	-5	V
I _C	collector current (DC)	-0.6	A
P _C	Collector dissipation	0.2	W
R _{θJA}	Thermal resistance junction to ambient	625	°C/W
T _J , T _{STG}	junction and storage temperature	-55 to +150	°C

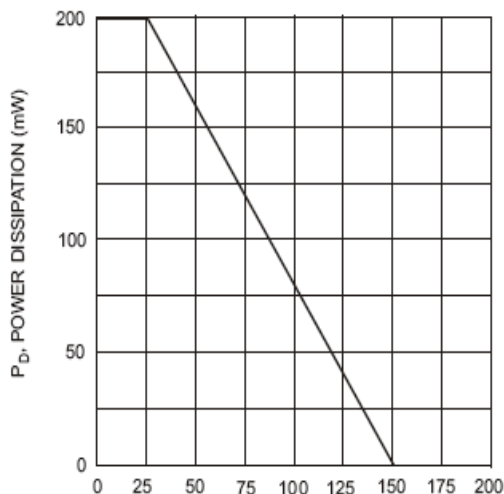
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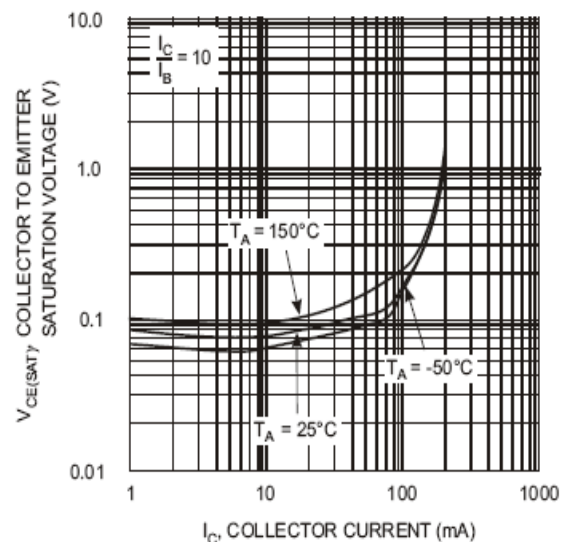
ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-100\mu\text{A}, I_E=0$	-160		
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1\text{mA}, I_B=0$	-150		
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-10\mu\text{A}, I_C=0$	-5		
I_{CBO}	collector cut-off current	$I_E=0; V_{CB} = -120\text{V}$	-	-50	nA
I_{EBO}	emitter cut-off current	$I_C=0; V_{EB} = -3\text{V}$	-	-50	nA
h_{FE}	DC current gain	$V_{CE}=-5\text{V}; I_C=-1\text{mA}$ $V_{CE}=-5\text{V}; I_C=-10\text{mA}$ $V_{CE}=-5\text{V}; I_C=-50\text{mA}$	50 60 50	- 240 -	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C=-50\text{mA}; I_B=-5\text{mA}$ $I_C=-10\text{mA}; I_B=-1\text{mA}$	-	-0.5 -0.2	V
$V_{BE(sat)}$	base-emitter saturation voltage	$I_C=-50\text{mA}; I_B=-5\text{mA}$ $I_C=-10\text{mA}; I_B=-1\text{mA}$	-	-1 -1	V
f_T	transition frequency	$I_C=-10\text{mA}; V_{CE} = -10\text{V},$ $f=100\text{MHz}$	100	300	MHz
NF	Noise figure	$I_C=-200\text{mA}, V_{CE}=-5.0\text{V},$ $f=100\text{MHz}$		8	dB

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



T_A, AMBIENT TEMPERATURE (°C)
Fig. 1, Max Power Dissipation vs Ambient Temperature



I_C, COLLECTOR CURRENT (mA)
Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

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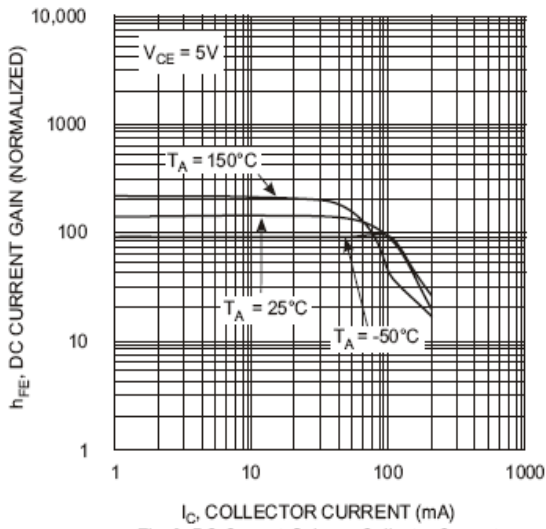


Fig. 3, DC Current Gain vs. Collector Current

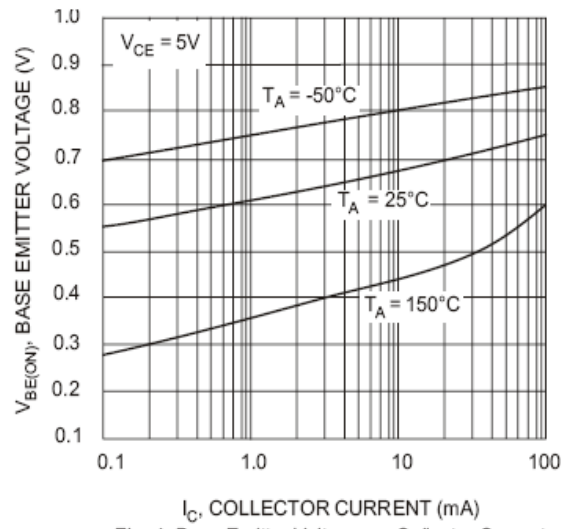


Fig. 4, Base Emitter Voltage vs. Collector Current

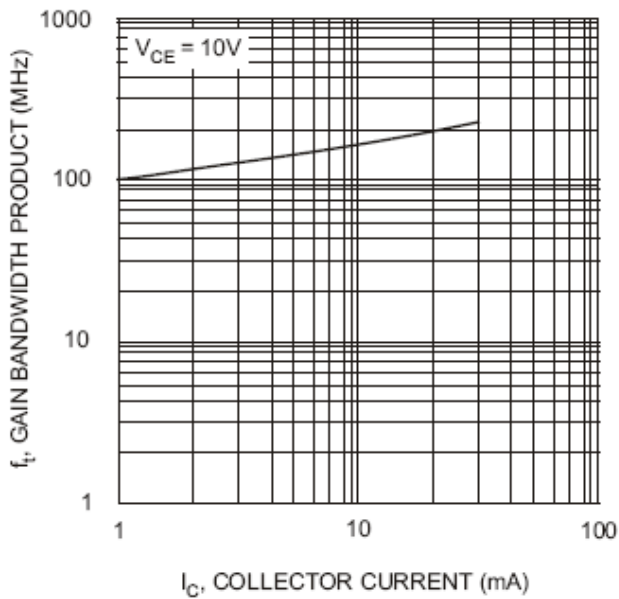


Fig. 5, Gain Bandwidth Product vs. Collector Current

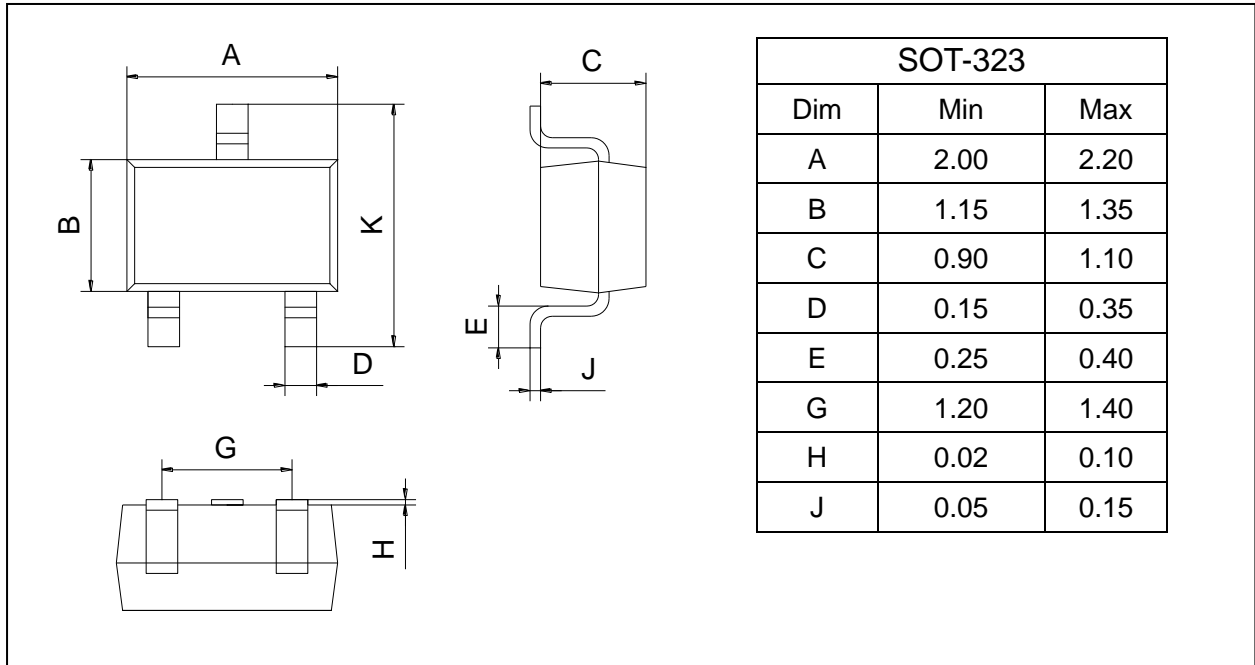
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PACKAGE OUTLINE

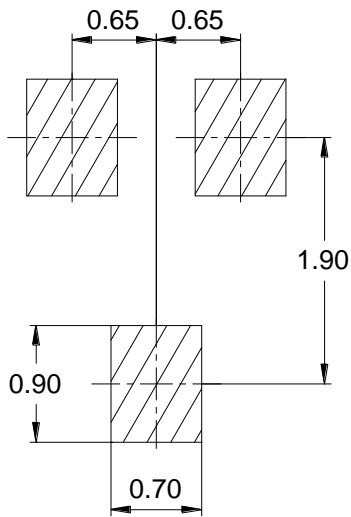
Plastic surface mounted package

SOT-323



SOT-323		
Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	0.25	0.40
G	1.20	1.40
H	0.02	0.10
J	0.05	0.15

SOLDERING FOOTPRINT



Unit: mm

PACKAGE INFORMATION

Device	Package	Shipping
MMST5401	SOT-323	3000 pcs / Tape & Reel